



PRODUCT DATA SHEET



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Datasheet



Resources



Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

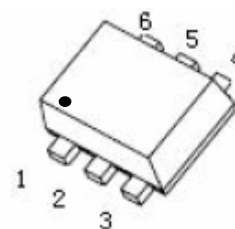
BVDSS	RDSON	ID
20V	150mΩ	1.0 A

FEATURE

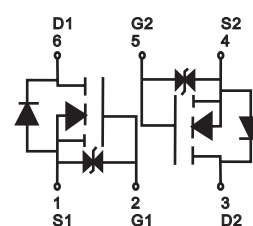
- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

APPLICATION

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift



SOT-563



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	20	V
Typical Gate-source voltage	V_{GS}	± 12	V
Continuous drain current ($t \leq 10\text{s}$)	I_D	1.0	A
Power dissipation(note1)	P_D	0.15	W
Thermal resistance from junction to ambient	$R_{\theta JA}$	833	$^{\circ}\text{C/W}$
Junction temperature	T_J	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55~ +150	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

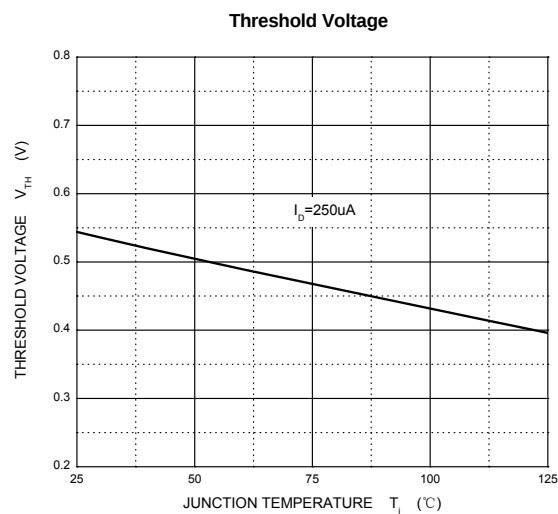
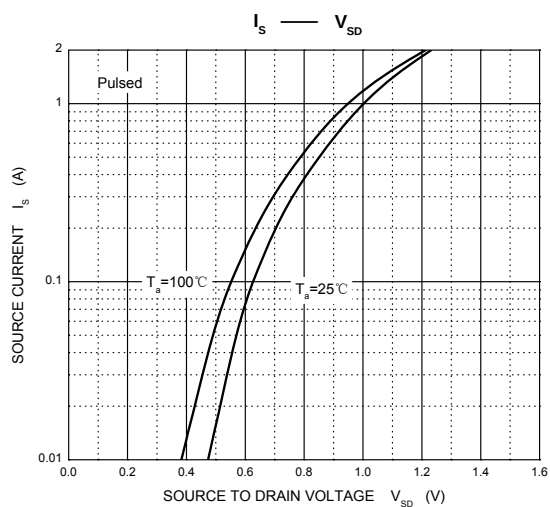
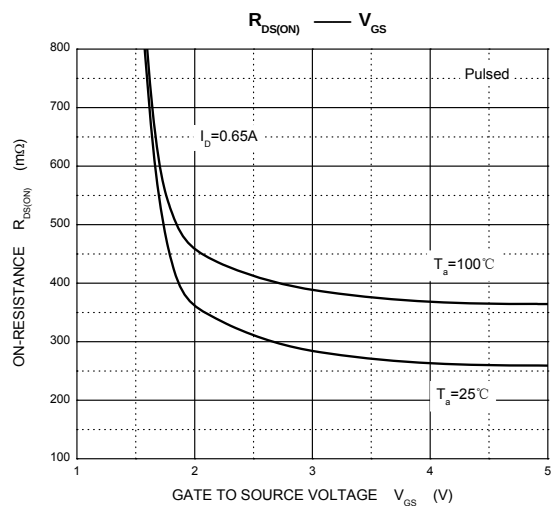
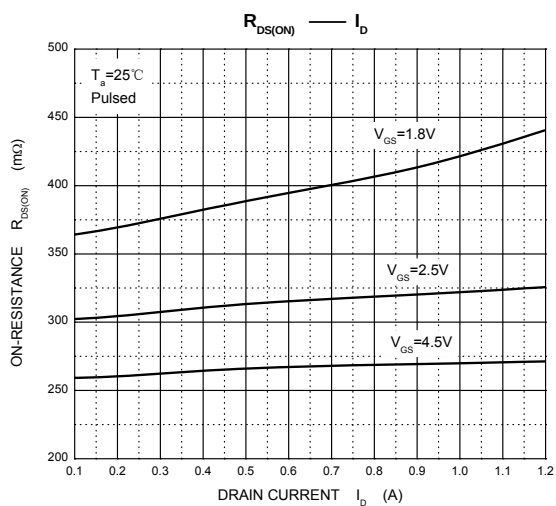
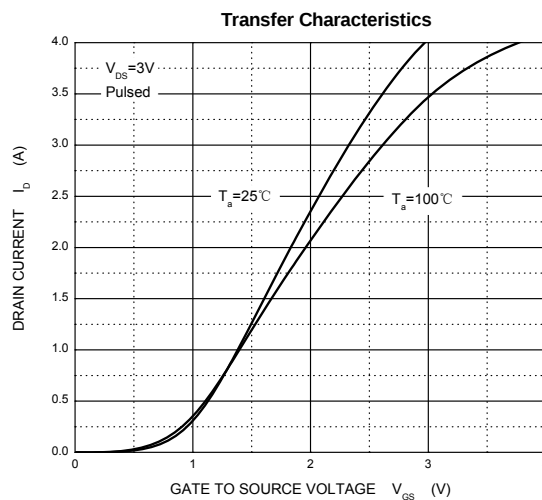
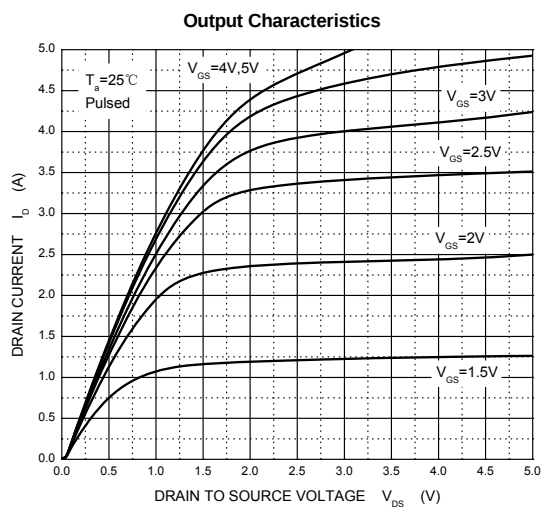
$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage (note 2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.35	0.54	1.1	V
Drain-source on-resistance (note 2)	R _{DS(on)}	V _{GS} =4.5V, I _D =0.95A		150	180	mΩ
		V _{GS} =2.5V, I _D =0.85A		220	250	mΩ
		V _{GS} =1.8V, I _D =0.75A		260	300	mΩ
Forward tranconductance (note 2)	g _{FS}	V _{DS} =10V, I _D =0.8A		1.6		S
Diode forward voltage(note 2)	V _{SD}	I _S =0.15A, V _{GS} = 0V			1.2	V
DYNAMIC PARAMETERS (note 3)						
Input Capacitance	C _{iss}	V _{DS} =16V, V _{GS} =0V, f =1MHz		79	120	pF
Output Capacitance	C _{oss}			13	20	pF
Reverse Transfer Capacitance	C _{rss}			9	15	pF
SWITCHING PARAMETERS(note 3)						
Turn-on delay time	t _{d(on)}	V _{GS} =4.5V, V _{DS} =10V, I _D =0.5A, R _{GEN} =10Ω		6.7		ns
Turn-on rise time	t _r			4.8		ns
Turn-off delay time	t _{d(off)}			17.3		ns
Turn-off fall time	t _f			7.4		ns
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V, I _D =7A		20		nC
Gate-Source Charge	Q _{gs}			1		nC
Gate-Drain Charge	Q _{gd}			4		nC

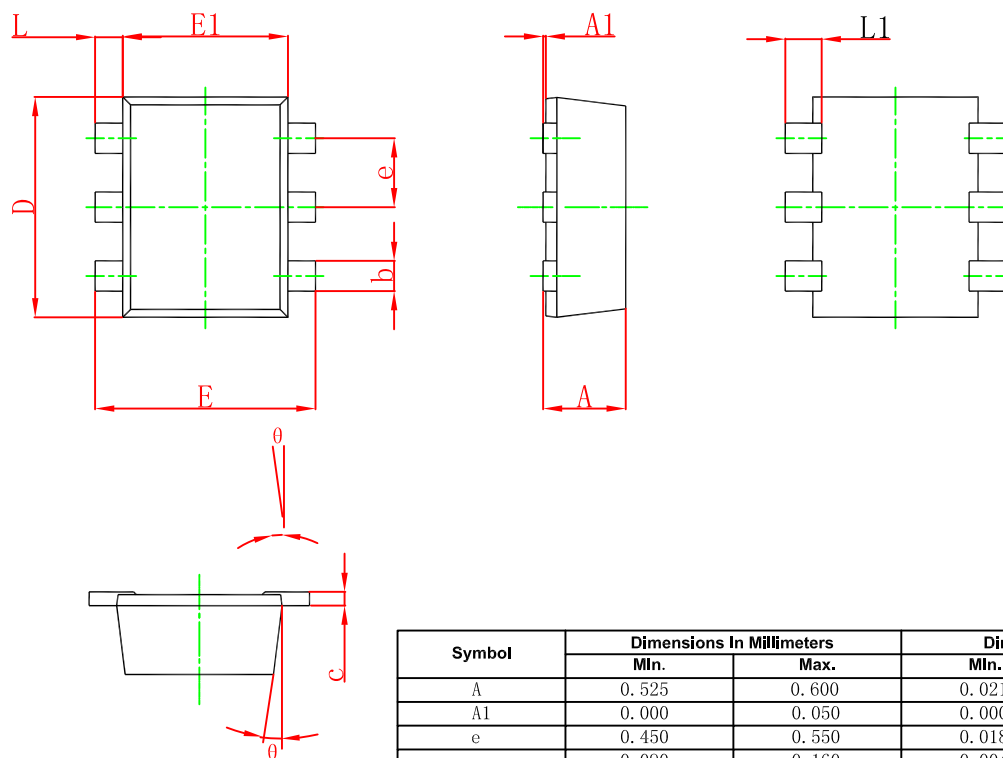
Notes :

1. Repetitive rating : Pulse width limited by junction temperature.
2. Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 0.5\%$.
3. Guaranteed by design, not subject to production testing.

Typical Characteristics

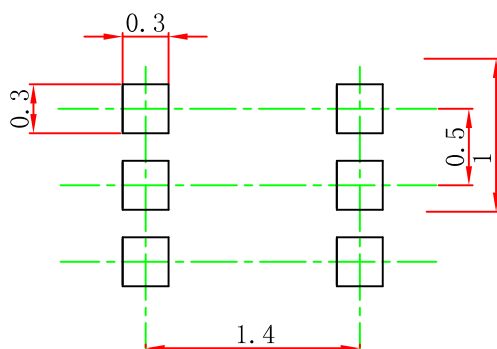


SOT-563 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Mln.	Max.	Mln.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	7 ⁰ REF.		7 ⁰ REF.	

SOT-563 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

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